

EAST: [10674612 asymmetrical cells.wsp:1]

FileViewEditToolsWindowHelp

Pending

Active

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L1: (811) (257/903).CCLS

L2: (172673) (asymmetry asymmetric \$4)

L3: (481) 2 adj (memory cell)

L4: (889) 2 near (memory cell)

L5: (111) and 4

(1) 09/948877

(1736) "KONINKLIJKE PHILIPS" as

(1) 10/674612

(2481584) memory cell

(0) first adj 10/674612

(54988) first adj (memory cell)

(51109) second adj (memory cell)

(11150) third adj (memory cell)

(120890) symmetries

(120880) symmetry

(876781) symmetry symmetric \$4 mirror

(686846) (asymmetry asymmetric \$4 mirror)

(166869) (asymmetry asymmetric \$4)

(22251) (first adj (memory cell)) near9 (second adj (memory cell))

(84) ((first adj (memory cell)) near9 (second adj (memory cell))) near9 (symmetry sym

(3295) (second adj (memory cell)) near9 (third adj (memory cell))

(3) ((first adj (memory cell)) near9 (second adj (memory cell))) near9 (symmetry sym

BrowseQueueClear

DBs:USPAT:US PGPUB:EPO:JPO:DERWENT:ICM:YDC

Default operator:OR

Plurals

+highlight all hit terms initially

1 and 4

ok 2004

	U	I	Inventor	Document	Issue	P	Title	Current	Current XN	Revised	S	C	P	Image	Doc	P
1			Rockett, Leo	US 2002002	20020	1	High-performance high-density CMOS sram c	257/389	257/903		R	F	F		US 200200	
2			Houston, The	US 2001005	20011	1	SRAM with write-back on read	257/390	257/903		R	F	F		US 200100	
3			Naffziger, Sa	US 6363008	20020	1	Asymmetric RAM cell	365/154	257/903		R	F	F		US 636300	
4			Park, Joon Y	US 6303966	20011	3	SRAM cell having overlapping access transis	257/393	257/379		R	F	F		US 630396	
5			Naffziger, Sa	US 6240009	20010	1	Asymmetric ram cell	365/154	257/903		R	F	F		US 624000	
6			Kim, Dong Su	US 6028340	20000	1	Static random access memory cell having a f	257/388	257/379		R	F	F		US 602834	
7			Lien, Chuen D	US 5790452	19980	7	Memory cell having asymmetrical source/dra	365/154	257/393		R	F	F		US 579045	
8			Orlowski, Ma	US 5567958	19981	1	High-performance thin-film transistor and SR	257/68	257/330		R	F	F		US 556795	
9			Yang, Ming-T	US 5481251	19951	1	Symmetric SRAM cell with buried N+ local i	257/379	257/903		R	F	F		US 548125	
10			Pfister, Jam	US 5458688	18951	1	Semiconductor memory cell and fabrication	257/69	257/377		R	F	F		US 545868	

Ready

NUM